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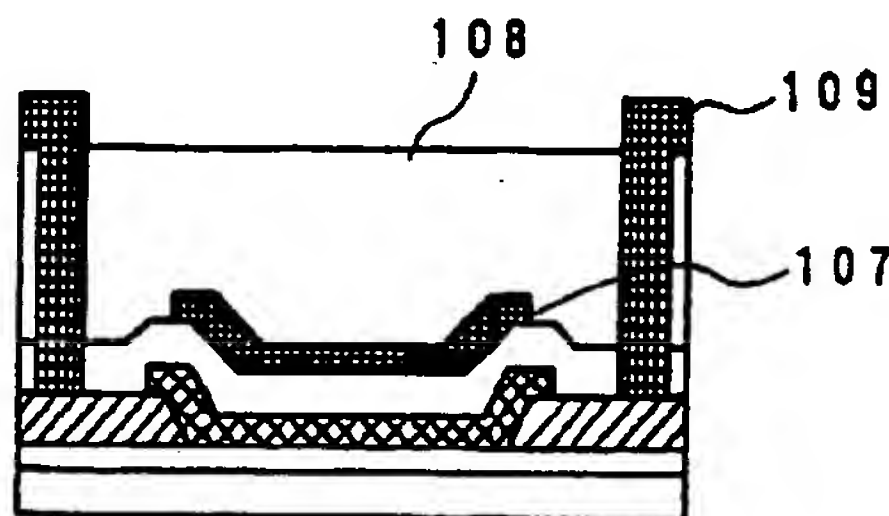
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(54) **Thin film semiconductor device, process for fabricating the same, and silicon film**

(57) There is disclosed a semiconductor device comprising a silicon film formed on a substrate having at least a surface formed of an insulative material, the sili-

con film being heat-treated at a temperature below 600 °C and being partially coated with a silicon oxide film formed by electronic cyclotron resonance plasma CVD.

Fig. 1E



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Title:

THIN FILM SEMICONDUCTOR DEVICE, PROCESS FOR FABRICATING THE  
SAME, AND SILICON FILM. ;

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ABSTRACT:

There is disclosed a semiconductor device comprising a silicon film formed on a substrate having at least a surface formed of an insulative material, the silicon film being heat-treated at a temperature below 600 DEG C and being partially coated with a silicon oxide film formed by electronic cyclotron resonance plasma CVD.